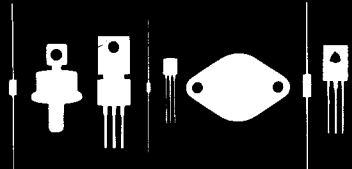


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148-B Lamar Street
West Babylon, New York 11704



SE9400
SE9401
SE9402

Silicon PNP Transistor

Darlington Power

JEDEC TO-220 Case

DESCRIPTION

The CENTRAL SEMICONDUCTOR SE9400, 01, 02 are Silicon PNP Epitaxial Base, Monolithic Diffused Resistor Type Darlington Construction Power Transistors designed for audio amplifiers and medium power linear and switching applications.

MAXIMUM RATINGS (T_C=25°C)

		<u>9400</u>	<u>9401</u>	<u>9402</u>
Collector to Emitter Voltage	V _{CEO}	60V	80V	100V
Collector to Base Voltage	V _{CBO}	60V	80V	100V
Emitter to Base Voltage	V _{EBO}	5V	5V	5V
Collector Current	I _C	10A	10A	10A
Power Dissipation	P _D	70W	70W	70W
Operating Junction Temperature	T _J	-65 to +150°C		
Storage Temperature	T _{stg}	-65 to +150°C		

ELECTRICAL CHARACTERISTICS (T_C=25°C)

<u>Symbol</u>	<u>Test Conditions</u>	<u>Min.</u>	<u>Max.</u>	<u>Unit</u>
I _{CBO}	V _{CE} =Rated V _{CEO}		200	uA
I _{EBO}	V _{EB} =5.0V		4.0	mA
I _{CEO}	V _{CE} =0.5×Rated V _{CEO}		500	uA
V _{CEO}	I _C =100mA	9400 9401 9402		V
		60		V
		80		V
		100		V
V _{CE(S)}	I _C =4.0A, I _B =16mA		2.0	V
V _{CE(S)}	I _C =7.5A, I _B =150mA		2.5	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =4.0A		2.5	V
V _{BE(ON)}	V _{CE} =3.0V, I _C =7.5A		3.0	V
h _{FE}	V _{CE} =3.0V, I _C =1.0A	750		-
h _{FE}	V _{CE} =3.0V, I _C =4.0A	1,000		-
h _{FE}	V _{CE} =3.0V, I _C =7.5A	100		-
h _{fe}	V _{CE} =3.0V, I _C =4.0A, f=1.0MHz	1.0		-



To-220

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